# Superconductivity in  $BiS_2$ -Based Layered Compounds

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#### **Abstract**

Crystal structure and physical properties of the novel  $Bis_2$ -based layered superconductors are briefly reviewed. Superconductivity in the  $Bis_2$ -based layered compounds is induced by electron doping into the  $Bis_2$  conduction layers. The superconducting properties seem to correlate with the crystal structure. Possible strategies for increasing transition temperature in this family are discussed.

## **Introduction**

Since the discovery of the cuprate layered superconductors, materials possessing a layered crystal structure have been one of the mostly-studied systems on exploration of new superconductors [1]. The discovery of the Fe-based superconductors in 2008 has also accelerated studies on new layered materials [2]. One of the reasons for the tremendous amount of attentions in the layered superconductors is the observation of unconventional paring mechanisms due to low-dimensional characteristics of conductive electrons. Another merit of layered materials in exploring for new superconductors is the variation of crystal structure. In general, the layered superconductors possess a crystal structure composed of an alternate stacking of a common superconducting layer and a blocking (spacer) layer. In the Fe-based family, the Fe<sub>2</sub>An<sub>2</sub> layers (An = P, As, S, Se or Te) could act as a common superconducting layer, and a lot of Fe-based superconductors have been discovered by changing the blocking layer structure [2-4]. Namely, if we discover a new type of superconducting layers, we can design a lot of layered superconductors. In 2012, the novel layered superconductors with a BiS<sub>2</sub>-based superconducting layer have been discovered [5,6]. So far, 11 superconductors have been discovered, and some notable characteristics have been observed in this family [7-11]. Here, the crystal structure and physical properties of the  $BiS_2$ -based superconductors are briefly reviewed.

#### **Crystal structure and superconducting properties**

Figure 1(a) and (b) show the schematic images of the crystal structure of typical BiS2-based superconductor  $LaOBiS<sub>2</sub>$  and  $Bi<sub>4</sub>O<sub>4</sub>S<sub>3</sub>$ , respectively. Both materials are composed of an alternate stacking of the BiS<sup>2</sup> double layers and the blocking layer. Electron carriers, which are essential for the appearance of superconductivity in the  $BiS_2$ -based family, can be generated (controlled) by modifying the structure and the composition at the blocking layers. In the  $REOBiS<sub>2</sub>$  system ( $RE = Rare$  earth), electron carriers can be generated upon a partial substitution of  $O^{2}$  by F [6], which is an electron-doping strategy used in the FeAs-based superconductors. In the  $Bi_4O_4S_3$  superconductor, partial defects at the  $(SO_4)^2$  site can provide electron carriers into the  $\text{BiS}_2$  layers [5].



Fig. 1. (a) Crystal structure of LaOBiS<sub>2</sub>. (b) Crystal structure of  $Bi_4O_4S_3$ . In this figure, the structure is depicted with full site occupancy: Namely, the elemental composition of the shown structure is  $Bi_6O_8S_5$ . In real, there would be ~50 % defects at the  $(SO<sub>4</sub>)<sup>2</sup>$  site, which corresponds to the composition of  $Bi<sub>4</sub>O<sub>4</sub>S<sub>3</sub>$ .

The physical properties of BiS<sub>2</sub>-based compounds are introduced with the data of the LaO<sub>1-*xFxBiS<sub>2</sub>*</sub> system. Figure 2(a) displays the temperature dependence of resistivity for  $LaOBiS<sub>2</sub>$  (parent phase) and  $LaO<sub>0.5</sub>F<sub>0.5</sub>BiS<sub>2</sub>$ . The parent phase exhibits semiconducting transport behavior. With the partial substitution of O by F, the resistivity decreases and superconducting transition is observed at ~3 K for LaO<sub>0.5</sub>F<sub>0.5</sub>BiS<sub>2</sub>. The superconducting properties can be enhanced by annealing the  $LaO<sub>0.5</sub>F<sub>0.5</sub>BiS<sub>2</sub>$  superconducting sample under high pressure (HP). Figure 2(b) shows the temperature dependence of resistivity for as-grown and HP-annealed LaO<sub>0.5</sub>F<sub>0.5</sub>BiS<sub>2</sub>. The onset of the transition temperature  $(T_c)$  is clearly enhanced from 3 to 10.6 K by the HP annealing [6,10]. It was found that the uniaxial strain (contraction) along the *c* axis is generated by the HP annealing [11]. These facts indicate that the optimization local structure is essential for the appearance of bulk superconductivity at a higher temperature in the BiS<sub>2</sub>-based superconductors. It was also reported that the application of external pressure could enhance the  $T_c$  of as-grown  $LaO<sub>0.5</sub>F<sub>0.5</sub>BiS<sub>2</sub>$ . Furthermore, the crystal structure analysis under HP showed that the structural transition from tetragonal to monoclinic was positively linked with the enhancement of  $T_c$  under high pressure [12]. Theoretical investigations suggested that the slight changes in the local crystal structure such as the *z* coordinate of S at the  $Bis<sub>2</sub>$  layer could largely affect the band structure [13,14]. In these regards, the correlation between superconductivity and local crystal structure should be important to understand the mechanisms and to enhance the  $T_c$  in the  $\text{BiS}_2$ -based superconductors.

Figure 3(a) shows the temperature dependence of normalized resistivity around superconducting transition for the typical BiS<sub>2</sub>-based superconductors, LaO<sub>0.5</sub>F<sub>0.5</sub>BiS<sub>2</sub> (HP-annealed), CeO<sub>0.3</sub>F<sub>0.7</sub>BiS<sub>2</sub> (HP-annealed),  $N dO_0$ <sub>7</sub>F<sub>0.3</sub>BiS<sub>2</sub> (as-grown) andBi<sub>4</sub>O<sub>4</sub>S<sub>3</sub> (as-grown). Here the transport data for the samples with the highest  $T_c$  in the respective systems are summarized. The midpoints of  $T_c$  are summarized in Fig. 3(b). To discuss the tendency of the  $T_c$ , the area where the superconducting properties  $(T_c)$  are optimized is highlighted with a green square. The optimized  $T_c$  in the LaOBiS<sub>2</sub> system is the highest. Then, the optimized  $T_c$  tends to decrease by changing the blocking layer structure in an order of La<sub>2</sub>O<sub>2</sub>, Ce<sub>2</sub>O<sub>2</sub>,  $Nd<sub>2</sub>O<sub>2</sub>$  and  $Bi<sub>4</sub>O<sub>4</sub>(SO<sub>4</sub>)$ . The tendency can be understand with the change in the ionic radius of the anion  $(La^{3+}, Ce^{3+}, Nd^{3+}$  and  $Bi^{3+}$ ) in the blocking layer. The ionic radius of the anion directly tune the *a* axis length in this family. In fact, the optimized  $T_c$  in the  $BiS_2$ -based superconductors well correlates with the length of the *a* axis.



Fig. 2. (a) Temperature dependence of resistivity for LaOBiS<sub>2</sub> and LaO<sub>0.5</sub>F0<sub>0.5</sub>BiS<sub>2</sub>. (b) Temperature dependence of resistivity for as-grown and HP-annealed  $LaO<sub>0.5</sub>FO<sub>0.5</sub>BiS<sub>2</sub>$ .



Fig. 3. (a) Temperature dependence of normalized resistivity around superconducting transition for the typical BiS<sub>2</sub>-based superconductors, LaO<sub>0.5</sub>F<sub>0.5</sub>BiS<sub>2</sub> (HP-annealed), CeO<sub>0.3</sub>F<sub>0.7</sub>BiS<sub>2</sub> (HP-annealed),  $NdO_{0.7}F_{0.3}BiS_2$  (as-grown) and  $Bi_4O_4S_3$  (as-grown). (b) Transition temperatures (midpoint) are summarized.

## **Strategies to enhance superconducting properties**

In the above, possible two structural parameters are suggested to be essential for superconductivity in the BiS<sup>2</sup> family. The first one is the local structure correlated with the uniaxial compression along the *a* axis, which can be optimized by applying high pressure. This should be essential for the appearance of bulk superconductivity in the respective systems. The other parameter is the length of the *a* axis, which can be tuned by changing the blocking layer. Unfortunately, the largest rare earth is La; hence, we cannot synthesize new REOBiS<sub>2</sub> materials with larger *a* axis. Therefore, we should discover new blocking layers. For example, the structure similar to  $Bi_6O_8S_5$ , Fig. 1(b), is a candidate. If the Bi could be substituted with rare earth, larger *a* axis could be obtained. Another strategy is to use a perovskite-oxide blocking layer, which is formed in the Fe-based superconductor  $Sr<sub>4</sub>Sc<sub>2</sub>O<sub>6</sub>Fe<sub>2</sub>P<sub>2</sub>$  [17].

Recently, superconductors with Bi-Se and Bi-Te conduction layers were discovered. Maziopa et al. reported that LaO<sub>0.5</sub>F<sub>0.5</sub>BiSe<sub>2</sub> with a structure similar to LaOBiS<sub>2</sub> showed superconductivity below 2.6 K [18,19]. Malliakas et al. reported that  $CSB_4T\epsilon_6$  exhibited superconductivity below 4.4 K by electron

carrier doping. The Bi-Te blocks of  $CSBi_4Te_6$  are similar to the NaCl structure as well as the BiS<sub>2</sub> layers. Therefore, superconductivity observed in doped  $\text{CsB}_{i_4}\text{Te}_6$  could be driven with the mechanisms same as the BiS<sub>2</sub>-based superconductors. Hence, replacement of BiS<sub>2</sub> layers by Bi-Se or Bi-Te layers could be a promising strategy for enhancing  $T_c$  of Bi-based superconductors.

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